DISCRETE SEMICONDUCTORS

DATA SHEET

BSP89

N-channel enhancement mode vertical D-MOS transistor

Product specification
File under Discrete Semiconductors, SC13b

April 1995





N-channel enhancement mode vertical D-MOS transistor

BSP89

FEATURES

- Direct interface to C-MOS, TTL, etc.
- · High-speed switching
- No secondary breakdown.

DESCRIPTION

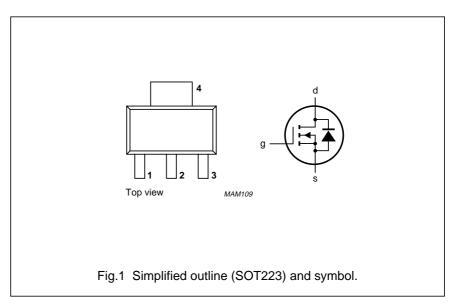
N-channel enhancement mode vertical D-MOS transistor in a SOT223 envelope, intended for use as a surface-mounted device in line current interrupters in telephone sets and for application in relay, high speed and line transformer drivers.

PINNING - SOT223

| PIN | PIN DESCRIPTION | | | | | |
|-----|-----------------|--|--|--|--|--|
| | Code: BSP89 | | | | | |
| 1 | gate drain | | | | | |
| 2 | drain | | | | | |
| 3 | source | | | | | |
| 4 | drain | | | | | |

QUICK REFERENCE DATA

| SYMBOL | PARAMETER | MAX. | UNIT |
|---------------------|-------------------------------|------|------|
| V _{DS} | drain-source voltage | 240 | V |
| I _D | DC drain current | 350 | mA |
| R _{DS(on)} | drain-source on-resistance | 6 | Ω |
| V _{GS(th)} | gate-source threshold voltage | 2 | V |



LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-------------------|---------------------------|---|------|------|------|
| V _{DS} | drain-source voltage | | _ | 240 | V |
| ±V _{GSO} | gate-source voltage | open drain | _ | 20 | V |
| I _D | DC drain current | | _ | 350 | mA |
| I _{DM} | peak drain current | | _ | 1.4 | Α |
| P _{tot} | total power dissipation | up to T _{amb} = 25 °C (note 1) | _ | 1.5 | W |
| T _{stg} | storage temperature range | | -65 | 150 | °C |
| Tj | junction temperature | | _ | 150 | °C |

THERMAL RESISTANCE

| SYMBOL | PARAMETER | THERMAL RESISTANCE | | |
|---------------------|-----------------------------------|--------------------|--|--|
| R _{th j-a} | from junction to ambient (note 1) | 83.3 K/W | | |

Note

1. Transistor mounted on an epoxy printed circuit board, 40 x 40 x 1.5 mm, mounting pad for the drain tab minimum 6 cm².

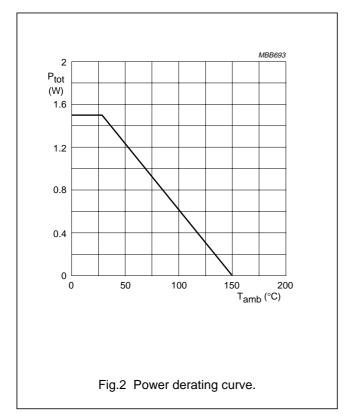
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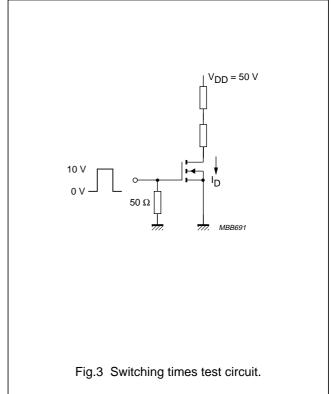
BSP89

CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified.

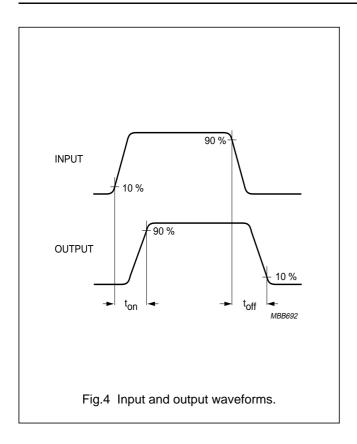
| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|----------------------|--------------------------------|---|------|------|------|------|
| V _{(BR)DSS} | drain-source breakdown voltage | $I_D = 10 \mu\text{A}; V_{GS} = 0$ | 240 | _ | _ | V |
| I _{DSS} | drain-source leakage current | V _{DS} = 60 V; V _{GS} = 0 | _ | _ | 200 | nA |
| ±I _{GSS} | gate-source leakage current | $\pm V_{GS} = 20 \text{ V}; V_{DS} = 0$ | _ | _ | 100 | nA |
| V _{GS(th)} | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{GS} = V_{DS}$ | 0.8 | _ | 2 | V |
| R _{DS(on)} | drain-source on-resistance | I _D = 340 mA; V _{GS} = 10 V | _ | 4 | 6 | Ω |
| | | $I_D = 340 \text{ mA}; V_{GS} = 4.5 \text{ V}$ | _ | _ | 10 | Ω |
| Y _{fs} | transfer admittance | I _D = 340 mA; V _{DS} = 25 V | 140 | 350 | _ | mS |
| C _{iss} | input capacitance | $V_{DS} = 25 \text{ V}; V_{GS} = 0; f = 1 \text{ MHz}$ | _ | 65 | 140 | pF |
| C _{oss} | output capacitance | $V_{DS} = 25 \text{ V}; V_{GS} = 0; f = 1 \text{ MHz}$ | _ | 20 | 30 | pF |
| C _{rss} | feedback capacitance | $V_{DS} = 25 \text{ V}; V_{GS} = 0; f = 1 \text{ MHz}$ | _ | 5 | 9 | pF |
| Switching ti | mes (see Figs 3 and 4) | | • | | | |
| t _{on} | turn-on time | $I_D = 250 \text{ mA}; V_{DD} = 50 \text{ V};$ $V_{GS} = 0 \text{ to } 10 \text{ V}$ | _ | 5 | 10 | ns |
| t _{off} | turn-off time | $I_D = 250 \text{ mA}; V_{DD} = 50 \text{ V};$ $V_{GS} = 0 \text{ to } 10 \text{ V}$ | _ | 20 | 30 | ns |





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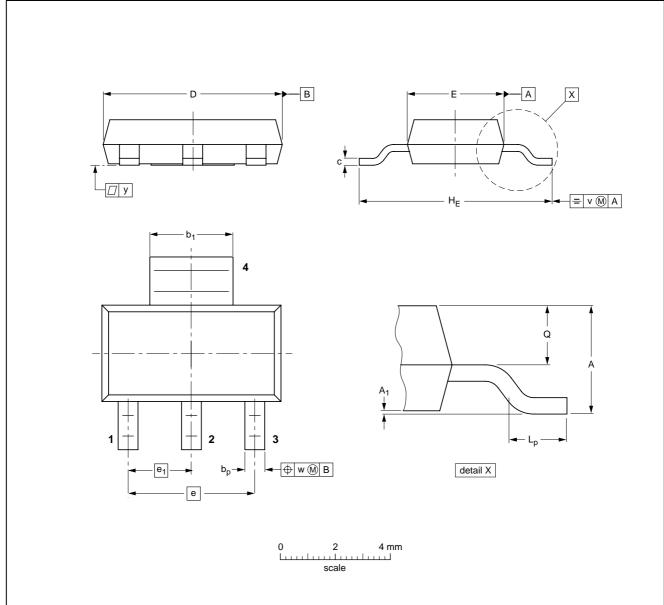
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PACKAGE OUTLINES

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



DIMENSIONS (mm are the original dimensions)

| UNIT | A | A ₁ | bp | b ₁ | С | D | E | е | e ₁ | HE | Lp | Q | ٧ | w | у |
|------|------------|----------------|--------------|----------------|--------------|------------|------------|-----|----------------|------------|------------|--------------|-----|-----|-----|
| mm | 1.8 1.5 | 0.10 0.01 | 0.80 0.60 | 3.1 2.9 | 0.32 0.22 | 6.7 6.3 | 3.7 3.3 | 4.6 | 2.3 | 7.3 6.7 | 1.1 0.7 | 0.95 0.85 | 0.2 | 0.1 | 0.1 |

| OUTLINE | | REFERENCES EUROPEAN , s | | | | | |
|---------|-----|-------------------------|------|--|------------|---------------------------------|--|
| VERSION | IEC | JEDEC | EIAJ | | PROJECTION | ISSUE DATE | |
| SOT223 | | | | | | 96-11-11 97-02-28 | |

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DEFINITIONS

| Data sheet status | | | | |
|---|---|--|--|--|
| Objective specification | This data sheet contains target or goal specifications for product development. | | | |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. | | | |
| Product specification | This data sheet contains final product specifications. | | | |
| Application information | | | | |
| Where application information is given, it is advisory and does not form part of the specification. | | | | |

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NOTES

Philips Semiconductors – a worldwide company

Argentina: see South America

Australia: 34 Waterloo Road, NORTH RYDE, NSW 2113,

Tel. +61 2 9805 4455, Fax. +61 2 9805 4466

Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213,

Tel. +43 1 60 101, Fax. +43 1 60 101 1210

Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,

220050 MINSK, Tel. +375 172 200 733, Fax. +375 172 200 773

Belgium: see The Netherlands **Brazil:** see South America

Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor,

51 James Bourchier Blvd., 1407 SOFIA, Tel. +359 2 689 211, Fax. +359 2 689 102

Canada: PHILIPS SEMICONDUCTORS/COMPONENTS,

Tel. +1 800 234 7381

China/Hong Kong: 501 Hong Kong Industrial Technology Centre,

72 Tat Chee Avenue, Kowloon Tong, HONG KONG,

Tel. +852 2319 7888, Fax. +852 2319 7700

Colombia: see South America
Czech Republic: see Austria

Denmark: Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S,

Tel. +45 32 88 2636, Fax. +45 31 57 0044 **Finland:** Sinikalliontie 3, FIN-02630 ESPOO, Tel. +358 9 615800, Fax. +358 9 61580920

France: 4 Rue du Port-aux-Vins, BP317, 92156 SURESNES Cedex,

Tel. +33 1 40 99 6161, Fax. +33 1 40 99 6427

Germany: Hammerbrookstraße 69, D-20097 HAMBURG,

Tel. +49 40 23 53 60, Fax. +49 40 23 536 300

Greece: No. 15, 25th March Street, GR 17778 TAVROS/ATHENS,

Tel. +30 1 4894 339/239, Fax. +30 1 4814 240

Hungary: see Austria

India: Philips INDIA Ltd, Shivsagar Estate, A Block, Dr. Annie Besant Rd. Worli, MUMBAI 400 018, Tel. +91 22 4938 541, Fax. +91 22 4938 722

Indonesia: see Singapore

Ireland: Newstead, Clonskeagh, DUBLIN 14, Tel. +353 1 7640 000, Fax. +353 1 7640 200

Israel: RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053, TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

Italy: PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3, 20124 MILANO, Tel. +39 2 6752 2531, Fax. +39 2 6752 2557

Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKYO 108,

Tel. +81 3 3740 5130, Fax. +81 3 3740 5077

Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL, Tel. +82 2 709 1412, Fax. +82 2 709 1415

Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,

Tel. +60 3 750 5214, Fax. +60 3 757 4880 **Mexico:** 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,

Tel. +9-5 800 234 7381

Middle East: see Italy

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,

Tel. +31 40 27 82785, Fax. +31 40 27 88399

New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,

Tel. +64 9 849 4160, Fax. +64 9 849 7811 **Norway:** Box 1, Manglerud 0612, OSLO, Tel. +47 22 74 8000, Fax. +47 22 74 8341

Philippines: Philips Semiconductors Philippines Inc., 106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI, Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

Poland: Ul. Lukiska 10, PL 04-123 WARSZAWA, Tel. +48 22 612 2831, Fax. +48 22 612 2327

Portugal: see Spain Romania: see Italy

Russia: Philips Russia, UI. Usatcheva 35A, 119048 MOSCOW,

Tel. +7 095 755 6918, Fax. +7 095 755 6919

Singapore: Lorong 1, Toa Payoh, SINGAPORE 1231,

Tel. +65 350 2538, Fax. +65 251 6500

Slovakia: see Austria Slovenia: see Italy

South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale,

2092 JOHANNESBURG, P.O. Box 7430 Johannesburg 2000,

Tel. +27 11 470 5911, Fax. +27 11 470 5494

South America: Rua do Rocio 220, 5th floor, Suite 51, 04552-903 São Paulo, SÃO PAULO - SP, Brazil, Tel. +55 11 821 2333, Fax. +55 11 829 1849 **Spain:** Balmes 22, 08007 BARCEL ONA

Tel. +34 3 301 6312. Fax. +34 3 301 4107

Sweden: Kottbygatan 7, Akalla, S-16485 STOCKHOLM,

Tel. +46 8 632 2000, Fax. +46 8 632 2745

Switzerland: Allmendstrasse 140, CH-8027 ZÜRICH, Tel. +41 1 488 2686, Fax. +41 1 481 7730

Taiwan: Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1,

TAIPEI, Taiwan Tel. +886 2 2134 2865, Fax. +886 2 2134 2874 Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd.,

209/2 Sanpavuth-Bangna Road Prakanong, BANGKOK 10260,

Tel. +66 2 745 4090, Fax. +66 2 398 0793

Turkey: Talatpasa Cad. No. 5, 80640 GÜLTEPE/ISTANBUL, Tel. +90 212 279 2770, Fax. +90 212 282 6707

Ukraine: PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,

252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Hayes, MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax. +44 181 754 8421 United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,

Tel. +1 800 234 7381 Uruguay: see South America

Vietnam: see Singapore

Yugoslavia: PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD,

Tel. +381 11 625 344, Fax.+381 11 635 777

For all other countries apply to: Philips Semiconductors, Marketing & Sales Communications, Building BE-p, P.O. Box 218, 5600 MD EINDHOVEN, The Netherlands, Fax. +31 40 27 24825

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